HM624257A Series

262,144-word × 4-bit High Speed CMOS Static RAM

The Hitachi HM624257A is a high speed 1 M Static RAM organized as 262,144-word × 4-bit. It realizes high speed access time (25/35 ns) and low power consumption, employing the advanced CMOS process technology and high speed circuit designing technology. It is most advantageous for the field where high speed and high density memory is required, such as the cache memory for main frame or 32-bit MPU.

The HM624257A, packaged in a 400-mil plastic SOJ is available for high density mounting.

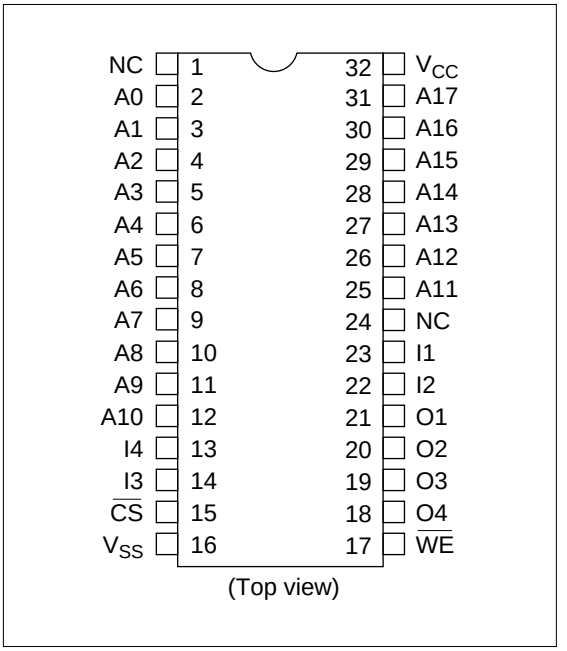
Features

- Single 5 V supply and high density 32-pin package (SOJ)
- High speed
  Access time: 25/35 ns (max)
- Low power dissipation
  Active mode: 350 mW (typ)
  Standby mode: 100 µW (typ)
- Completely static memory
  No clock or timing strobe required
- Equal access and cycle time
- Directly TTL compatible
  All inputs and outputs

Ordering Information

Type No.	Access time	Package
HM624257AJP-25	25 ns	400-mil 32-pin plastic SOJ (CP-32D)
HM624257AJP-35	35 ns	
HM624257ALJP-25	25 ns	
HM624257ALJP-35	35 ns	

Pin Arrangement

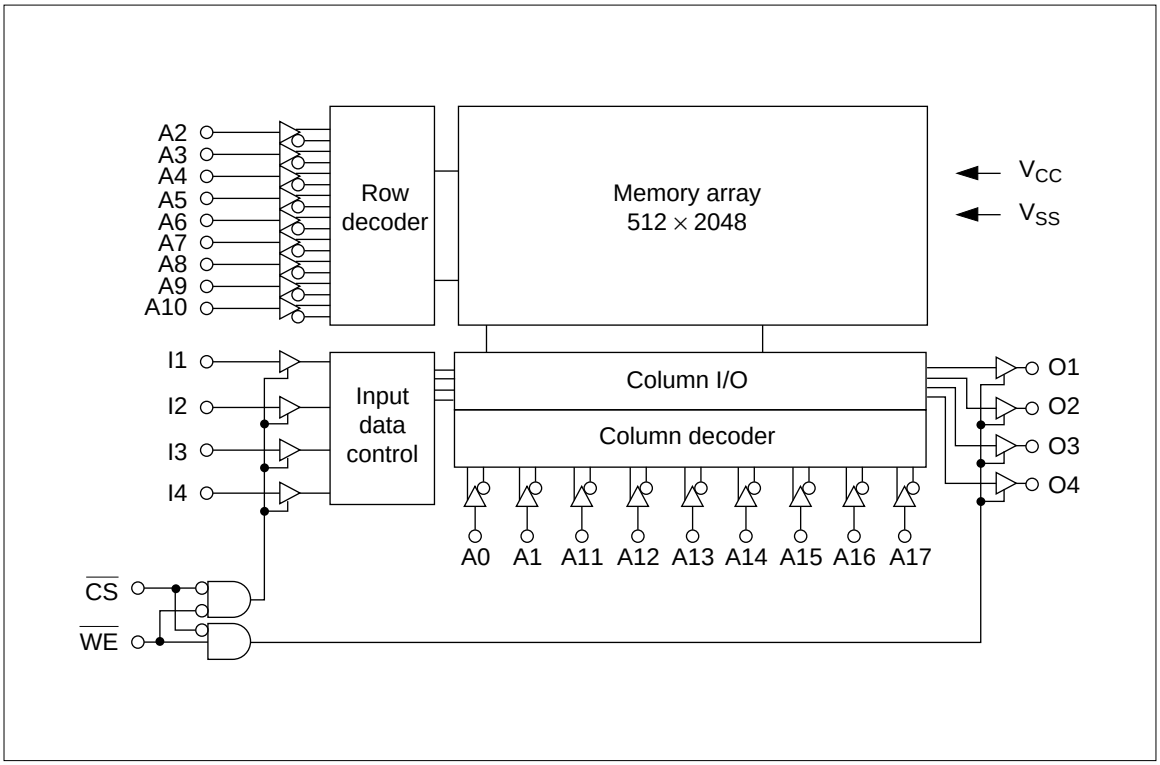


(Top view)

Pin Description

Pin name	Function
A0 – A17	Address
I1 – I4	Data input
O1 – O4	Data output
$\overline{CS}$	Chip select
$\overline{WE}$	Write enable
V_{CC}	Power supply
V_{SS}	Ground

Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	Vin	–0.5[*1] to +7.0	V
Power dissipation	P_T	1.0	W
Operating temperature range	Topr	0 to +70	°C
Storage temperature range	Tstg	–55 to +125	°C
Storage temperature range under bias	Tbias	–10 to +85	°C

Note: 1. Vin min = –2.0 V for pulse width ≤ 10 ns.

Function Table

$\overline{CS}$	$\overline{WE}$	Mode	V_{CC} current	Dout pin	Ref. cycle
H	X	Not selected	I_{SB}, I_{SB1}	High-Z	—
L	H	Read	I_{CC}	Dout	Read cycle (1) – (2)
L	L	Write	I_{CC}	High-Z	Write cycle (1) – (2)

Note: X : H or L

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input high (logic 1) voltage	V_{IH}	2.2	—	6.0	V
Input low (logic 0) voltage	V_{IL}	–0.5*1	—	0.8	V

Note: 1. V_{IL} min = –2.0 V for pulse width ≤ 10 ns.

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, V_{SS} = 0 V)

		HM624257A-25/35				
Parameter	Symbol	Min	Typ*1	Max	Unit	Test conditions
Input leakage current	$\|I_{LI}\|$	—	—	2.0	µA	V_{CC} = max, Vin = V_{SS} to V_{CC}
Output leakage current	$\|I_{LO}\|$	—	—	2.0	µA	$\overline{CS}$ = V_{IH}, $V_{I/O}$ = V_{SS} to V_{CC}
Operating power supply current	I_{CC}	—	—	120	mA	$\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA, min cycle
Standby power supply current	I_{SB}	—	—	40	mA	$\overline{CS}$ = V_{IH}, min cycle
Standby power supply current (1)	I_{SB1}	—	0.02	2.0	mA	$\overline{CS}$ ≥ V_{CC} – 0.2 V, 0 V ≤ Vin ≤ 0.2 V or Vin ≥ V_{CC} – 0.2V
	I_{SB1}*2	—	—	100*2	µA	
Output low voltage	V_{OL}	—	—	0.4	V	I_{OL} = 8 mA
Output high voltage	V_{OH}	2.4	—	—	V	I_{OH} = –4 mA

Notes: 1. Typical values are at V_{CC} = 5.0 V, Ta = +25°C and not guaranteed.
2. LJP version

Capacitance (Ta = 25°C, f = 1 MHz)*1

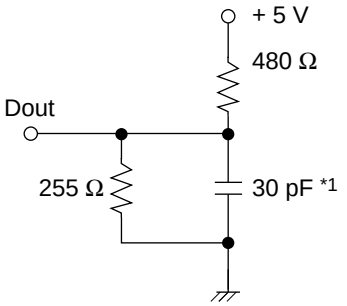
Parameter	Symbol	Min	Max	Unit	Test conditions
Input capacitance	Cin	—	5	pF	Vin = 0 V
Output capacitance	Cont	—	8	pF	Vout = 0 V

Note: 1. This parameter is sampled and not 100% tested.

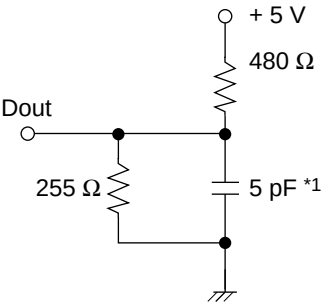
AC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, unless otherwise noted.)

Test Conditions

- Input pulse levels: 0 V to 3.0 V
- Input rise and fall times: 4 ns
- Input timing reference levels: 1.5 V
- Output timing reference levels: 1.5 V
- Output load: See figures



Output load (A)



Output load (B)
(For t_{HZ} , t_{LZ}, $t_{WZ,\ and}$ t_{OW})

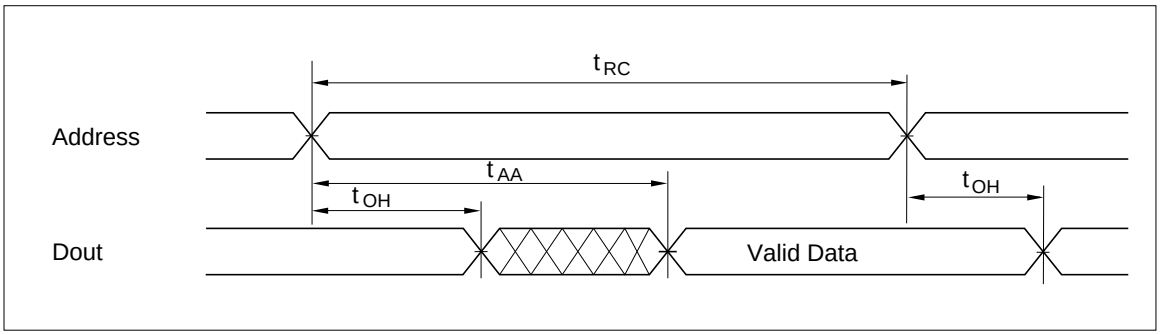
Note: 1. Including scope and jig

Read Cycle

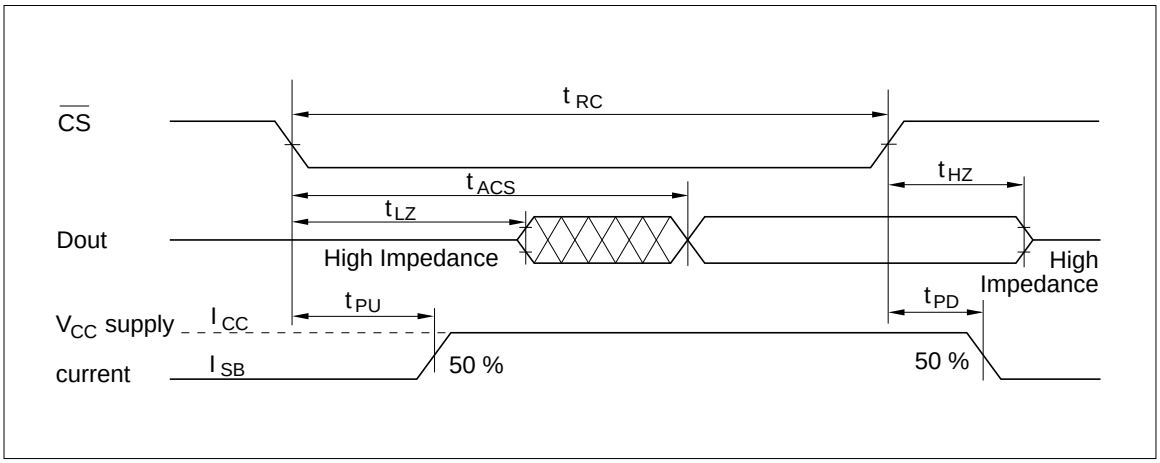
		HM624257A-25		HM624257A-35		
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Unit**
Read cycle time	t_{RC}	25	—	35	—	ns
Address access time	t_{AA}	—	25	—	35	ns
Chip select access time	t_{ACS}	—	25	—	35	ns
Output hold from address change	t_{OH}	5	—	5	—	ns
Chip selection to output in low-Z	t_{LZ}*1	5	—	5	—	ns
Chip deselection to output in high-Z	t_{HZ}*1	0	12	0	15	ns
Chip selection to power up time	t_{PU}	0	—	0	—	ns
Chip deselection to power down time	t_{PD}	—	15	—	25	ns

Notes: 1. Transition is measured ±200 mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.

Read Timing Waveform (1) *1, *2



Read Timing Waveform (2) *1, *3



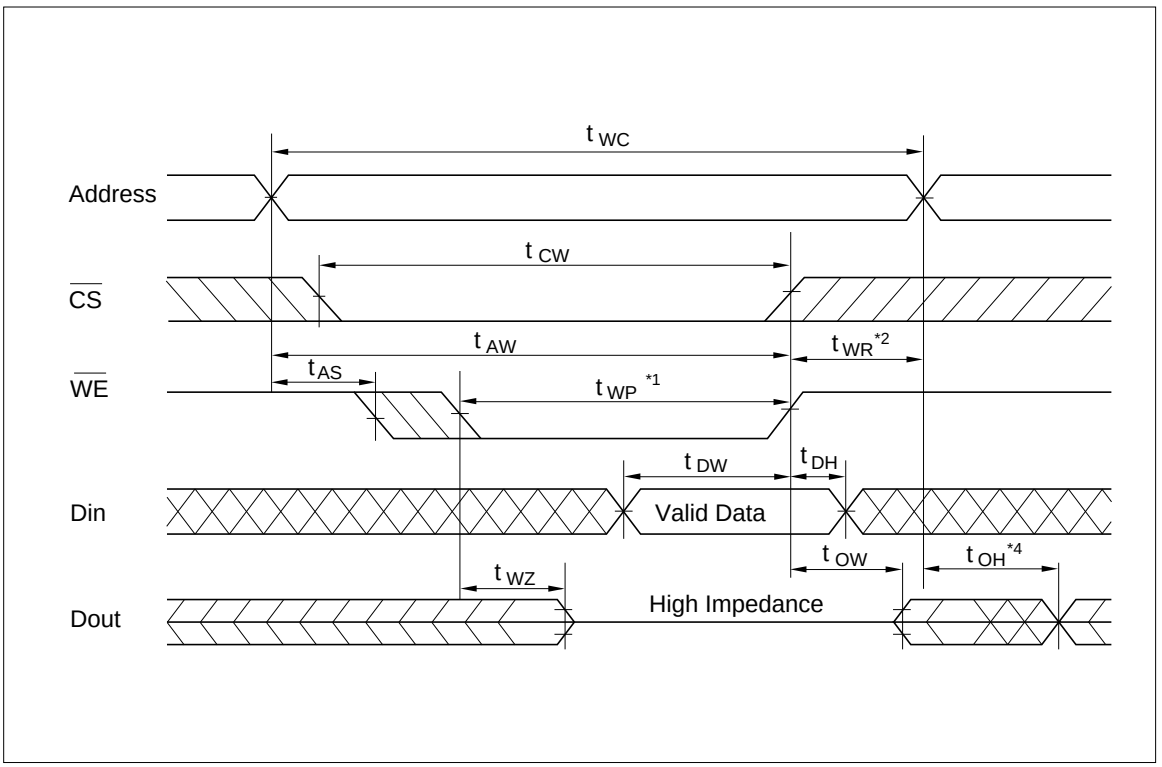
Notes: 1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected, $\overline{CS}$ = V_{IL}.
3. Address valid prior to or coincident with $\overline{CS}$ transition Low.

Write Cycle

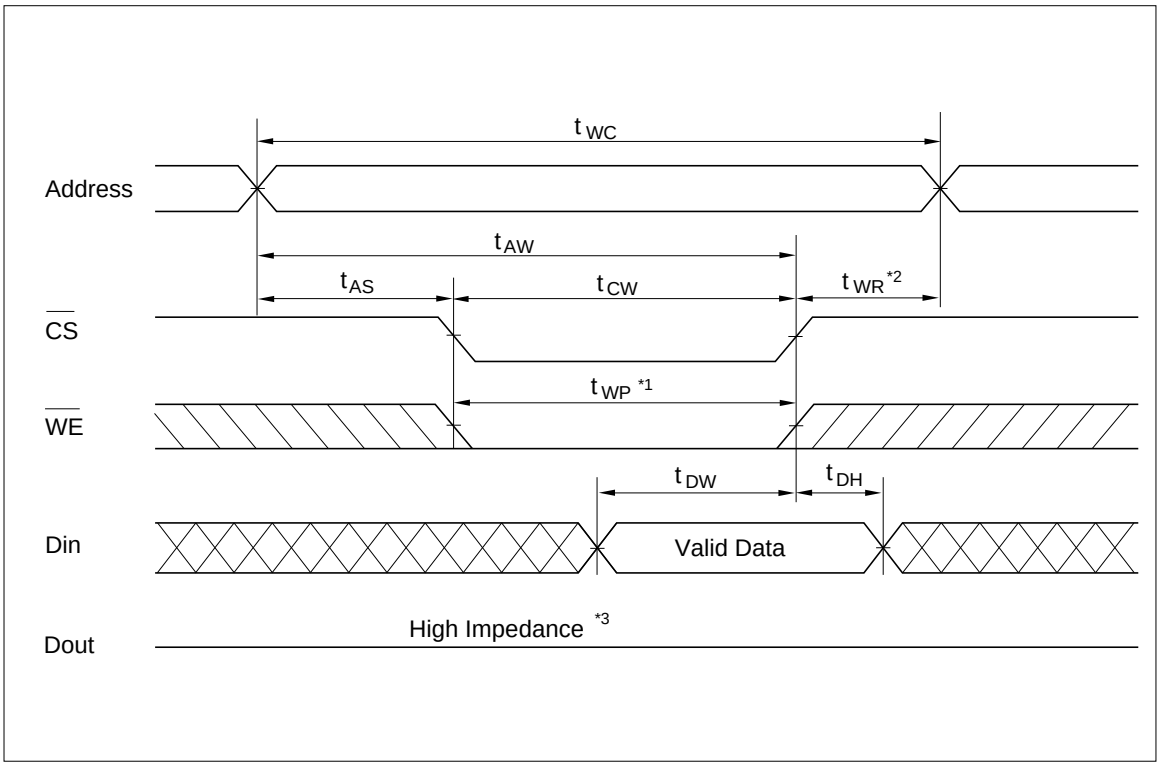
Parameter	Symbol	HM624257A-25 Min	HM624257A-25 Max	HM624257A-35 Min	HM624257A-35 Max	Unit
Write cycle time	t_{WC}	25	—	35	—	ns
Chip selection to end of write	t_{CW}	17	—	25	—	ns
Address valid to end of write	t_{AW}	20	—	30	—	ns
Address setup time	t_{AS}	0	—	0	—	ns
Write pulse width	t_{WP}	17	—	25	—	ns
Write recovery time	t_{WR}	0	—	0	—	ns
Data valid to end of write	t_{DW}	15	—	20	—	ns
Data hold time	t_{DH}	0	—	0	—	ns
Write enabled to output in high-Z	t_{WZ}*1	0	15	0	15	ns
Output active from end of write	t_{OW}*1	0	—	0	—	ns

Note: 1. Transition is measured ±200 mV from steady state voltage with Load (B). This parameter is sampled and not 100% tested.

Write Timing Waveform (1) ($\overline{WE}$ Controlled)



Write Timing Waveform (2) ($\overline{CS}$ Controlled)



Notes:
1. A write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$.
2. t_{WR} is measured from the earlier of $\overline{CS}$ or $\overline{WE}$ going high to the end of write cycle.
3. If the $\overline{CS}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, the output buffers remain in a high impedance state.
4. Dout is the same phase of write data of this write cycle, if t_{WR} is long enough.

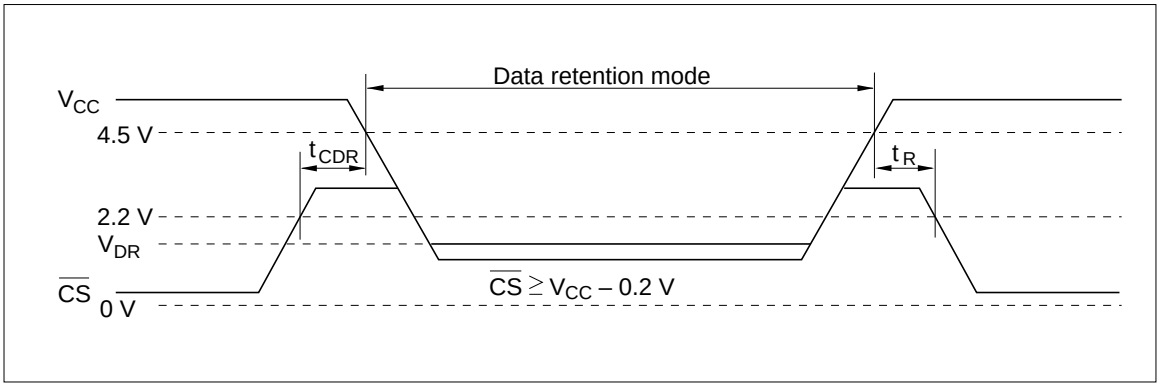
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

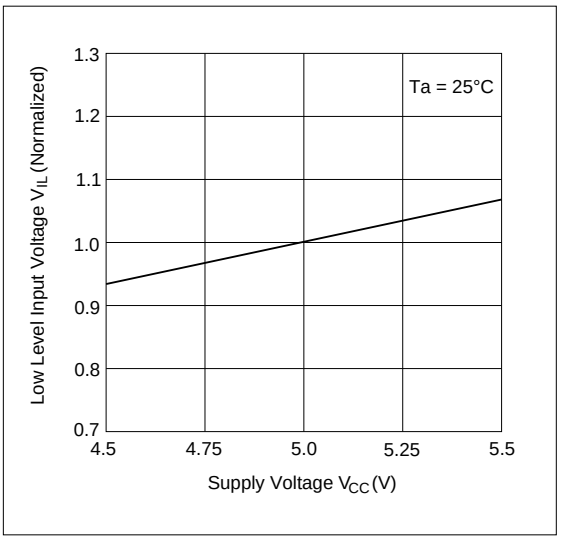
This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$\overline{CS} \geq V_{CC} - 0.2$ V, $Vin \geq V_{CC} - 0.2$ V or $0\ V \leq Vin \leq 0.2$ V
Data retention current	I_{CCDR}	—	2	50*1	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

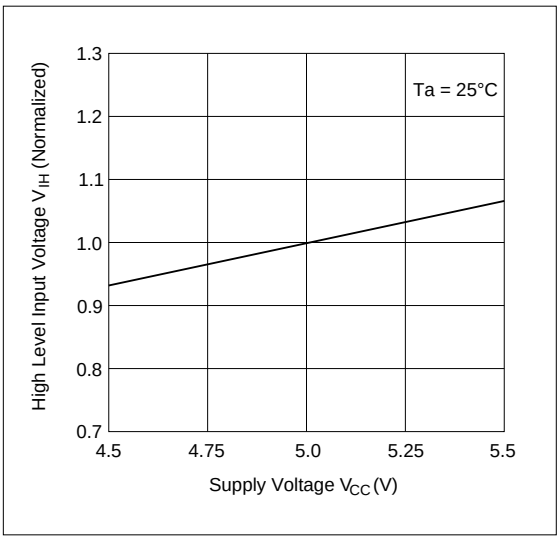
Note: 1. V_{CC} = 3.0 V

Low V_{CC} Data Retention Timing Waveform

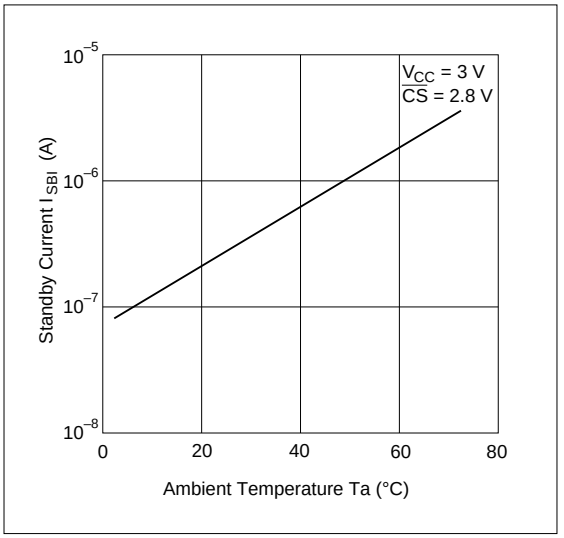




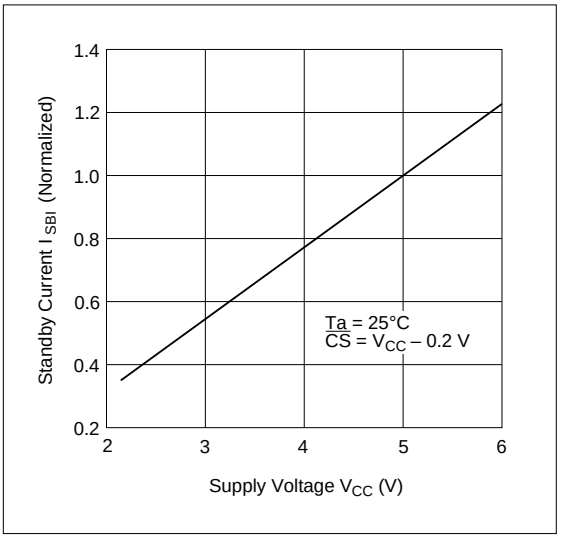
Low Level Input Voltage vs. Supply Voltage



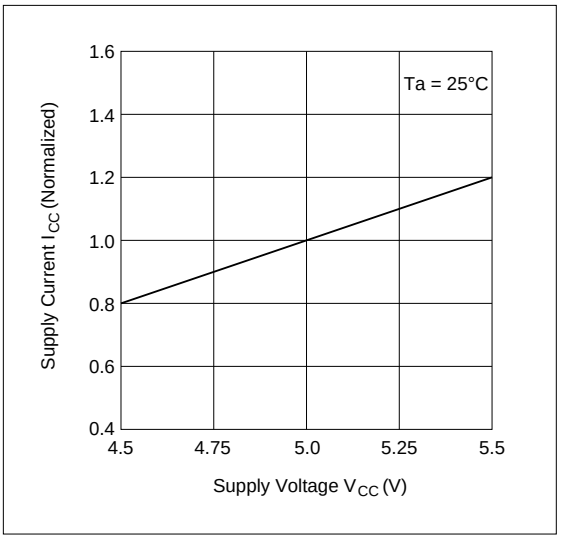
High Level Input Voltage vs. Supply Voltage



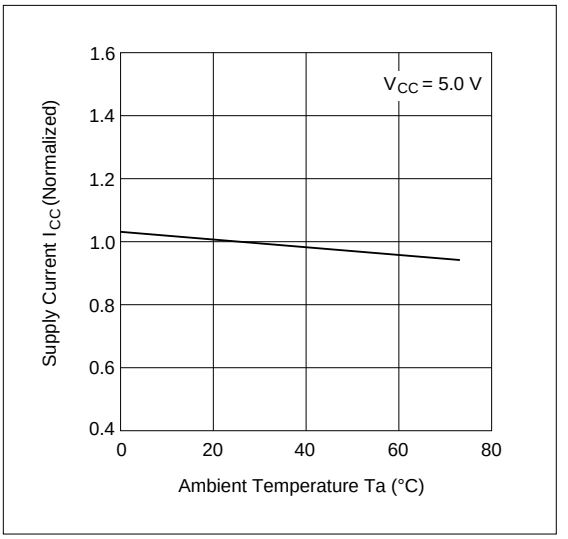
Standby Current vs. Ambient Temperature



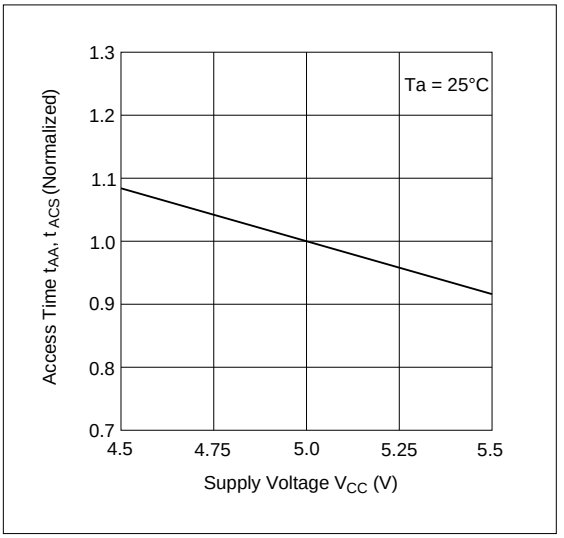
Standby Current vs. Supply Voltage



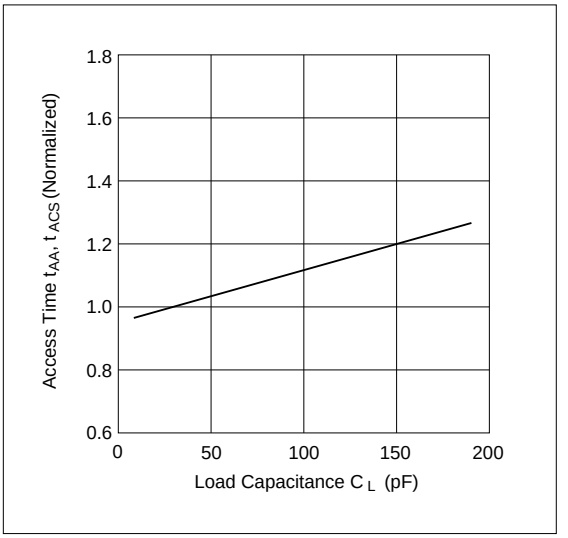
Supply Current vs. Supply Voltage



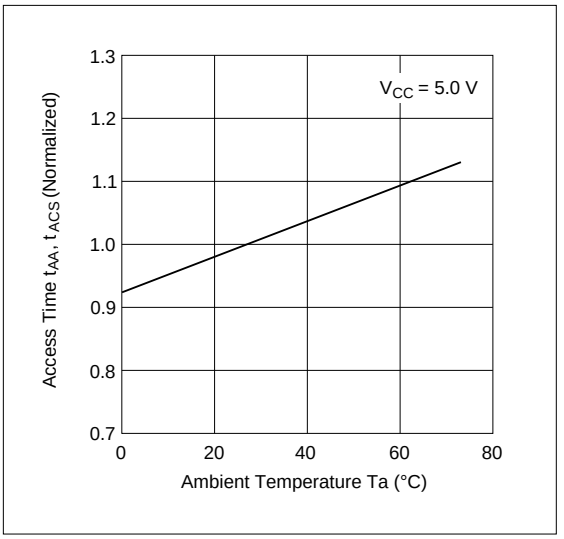
Supply Current vs. Ambient Temperature



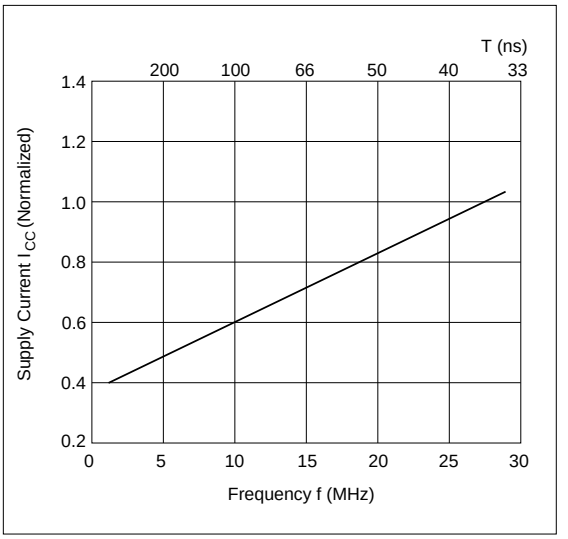
Access Time vs. Supply Voltage



Access Time vs. Load Capacitance



Access Time vs. Ambient Temperature



Supply Current vs. Frequency